A short summary from the 27th HWG meeting:

Uladzimir Kruchonak gave the presentation "Radiation hardness tests at JINR":

- two new GaAs sensors (with and without junction) and two Si n-type sensors (from  USCS and Russian) were irradiated with 800 MeV electrons in LINAC-800 at JINR

- sensor sizes were from 4x4 mm^2 to 5x5 mm^2, thickness 300um

- irradiations were done in room temperature in several steps so that each sensor received in total more than 1.5 MGy

- CCE and I-V were measured after each step

- for Si sensors the leakage current increased few orders of magnitude and reached few tens of uA at the end

- for GaAs maximum current was few uA

- the CCE for GaAs decreased an order of magnitude, and much less for Si

- but the noise increased very little for GaAs and much more for Si, so that after total irradiation it was still possible to distinguish

the MIP peak from the noise for GaAs sensors, while it was not possible for Si sensors

- the performance of Si sensors after irradiation could be improved significantly by cooling (resulting in the drop of leakage current)

Wolfgang proposed to irradiate also p-type Si sensors for which better hardness could be expected and for which irradiations with electronics have not yet been done.

This was our last meeting in 2016.

 Merry Christmas and a Happy New Year! [pl.bab.la]

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